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(54) **METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

Provided is a method for manufacturing a semiconductor device whose electric characteristics are prevented from being varied and whose reliability is improved. In the method, an insulating film is formed over an oxide semiconductor film, a buffer film is formed over the insulating film, oxygen is added to the buffer film and the insulating film, a conductive film is formed over the buffer film to which oxygen is added, and an impurity element is added to the oxide semiconductor film using the conductive film as a mask. An insulating film containing hydrogen and overlapping with the oxide semiconductor film may be formed after the impurity element is added to the oxide semiconductor film.

